

Vishay Siliconix

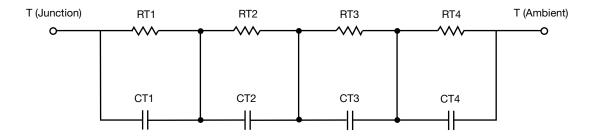
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	C VALUES FOR TANK CONFIGURATION				
	THERMAL RES	SISTANCE (°C/W)			
Junction to	Ambient	Case	Foot		
RT1	n/a	19.4839m	n/a		
RT2	n/a	44.1809m	n/a		
RT3	n/a	105.5655m	n/a		
RT4	n/a	280.7697m	n/a		
·	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	27.0747m	n/a		
CT2	n/a	75.9616m	n/a		
CT3	n/a	52.9147m	n/a		
CT4	n/a	100.0188m	n/a		

Note

• n/a indicates not applicable

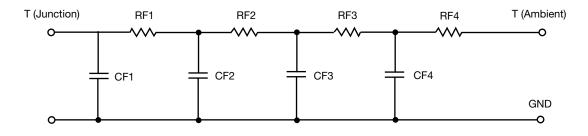
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



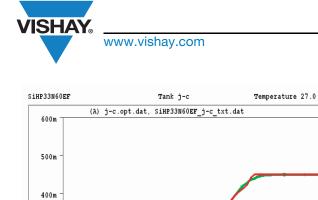
THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	n/a	60.8713m	n/a		
RF2	n/a	174.7882m	n/a		
RF3	n/a	147.2818m	n/a		
RF4	n/a	67.0587m	n/a		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	11.1751m	n/a		
CF2	n/a	14.0301m	n/a		
CF3	n/a	88.8046m	n/a		
CF4	n/a	6.3132m	n/a		

Note

• n/a indicates not applicable

SiHP33N60EF_RC

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100ms

1.0s

15:44:48

10ms

Time Page 1

300m

200m

100m

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0 T 100us V (CT1:1)

1.0ms "j-c"

